Product data sheet

1. General description

Dual, common cathode, ultrafast, epitaxial rectifier diodes in a TO220F package.

2. Features and benefits

- · Low forward voltage drop
- Fast switching
- Soft reverse recovery characteristics
- · High thermal cycling performance

3. Applications

• Output rectifiers in high frequency switched-mode power supplies.

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values		Unit	
Absolute	maximum rating					
V_{RRM}	repetitive peak reverse voltage		500			V
I _{O(AV)}	average output current	δ = 0.5 ; T _h ≤ 84 °C; square-wave pulse; both diodes conducting		10		А
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_h \le 108 °C$; square-wave pulse; per diode	10			А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	65		А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	72			А
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics		'			
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; per diode; <u>Fig. 6</u>	-	1.05	1.4	V
		I _F = 5 A; T _j = 150 °C; per diode; <u>Fig. 6</u>	-	0.95	1.05	V
Dynamic	characteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ per diode}; \underline{\text{Fig. 7}}$	-	28	60	ns

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BYT28X-500

Dual ultrafast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode	mb	
2	K	cathode		A1
3	A2	anode		
mb	n.c.	mounting base; isolated		sym125

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYT28X-500	TO-220F	BYT28X-500Q	Tube	50	SOT186A	14-Nov-2013

7. Marking

Table 4. Marking codes

Type number	Marking codes			
	Assembly factory: d	Assembly factory: A		
BYT28X-500	BYT28X 500 PJdxxxx xx	BYT28X 500 PJAxxxx xx		

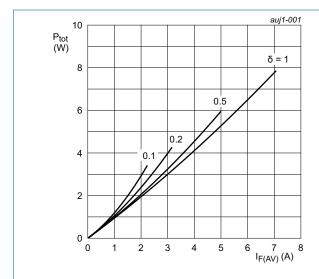
Dual ultrafast power diode

8. Limiting values

Table 5. Limiting values

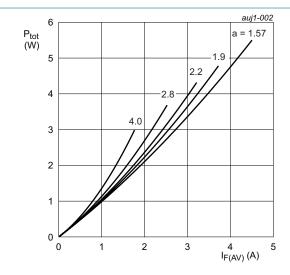
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		500	V
V_{RWM}	crest working reverse voltage		500	V
V_R	reverse voltage	DC	500	V
I _{O(AV)}	average output current	δ = 0.5 ; T _h ≤ 84 °C; square-wave pulse; both diodes conducting	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t_p = 25 µs; $T_h \le$ 108 °C; square-wave pulse; per diode	10	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	65	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	72	А
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		150	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 0.918 \text{ V; } R_s = 0.0273 \text{ }\Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 0.918 V; R_s = 0.0273 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

Dual ultrafast power diode

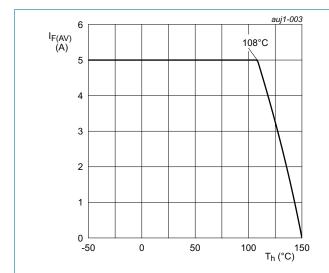


Fig. 3. Forward current as a function of heatsink temperature; maximum values; per diode

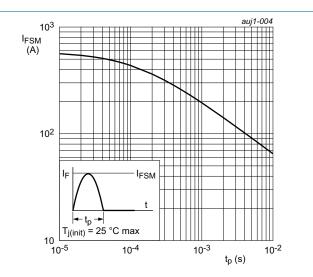


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to	with heatsink compound; per diode; Fig. 5	-	-	7	K/W
	heatsink	with heatsink compound; both diodes conducting; Fig. 5	-	-	5.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

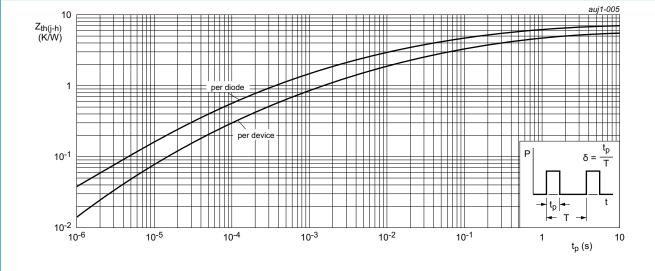


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

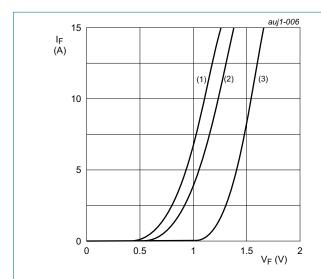
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

Dual ultrafast power diode

11. Characteristics

Table 8. Characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _F	forward current	$I_F = 5 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$	-	1.05	1.4	V
		$I_F = 5 \text{ A}; T_j = 150 ^{\circ}\text{C}; \text{ per diode}; Fig. 6$	-	0.95	1.05	V
I _R	reverse current	$V_R = 500 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ per diode}$	-	2	10	μA
		V _R = 500 V; T _j = 100 °C; per diode	-	0.17	0.5	mA
Dynamic	characteristics					_
Q_r	reverse charge	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; per diode; Fig. 7	-	32	60	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; per diode; Fig. 7	-	28	60	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/µs}$; $T_i = 25 ^{\circ}\text{C}$; per diode; Fig. 7	-	2	3	А



 V_{o} = 0.918 V; R_{s} = 0.0273 Ω

(1) T_i = 150 °C; typical values

(2) $T_j = 150$ °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode

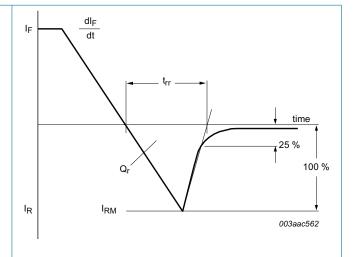
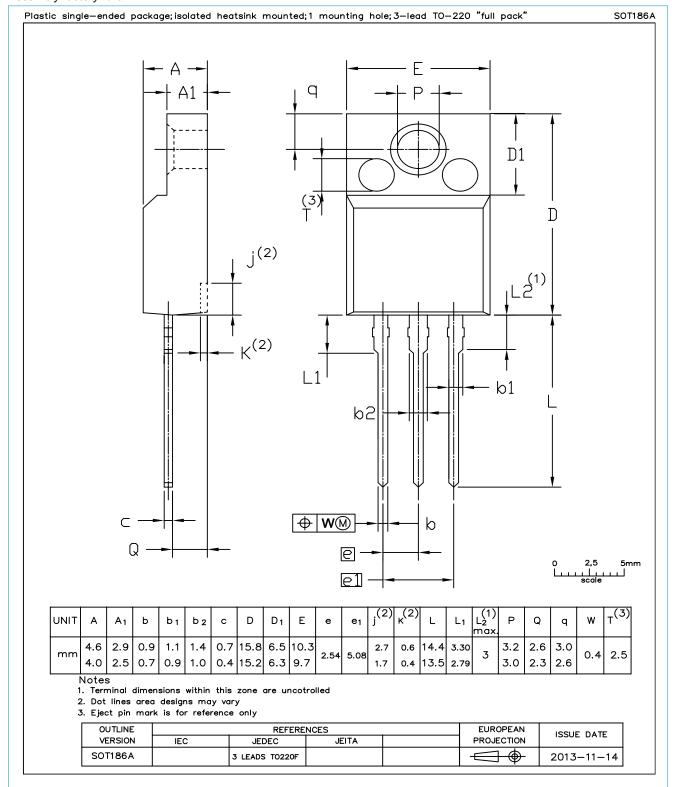


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline

Assembly factory: d & A



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13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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